

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|--------------------------------------|------------------|---------|------------------|
| S1 | 1220 | (438/592).CCLS. | US-PGPUB; USPAT; USOCR; JPO | OR | OFF | 2005/05/20 09:19 |
| S2 | 349 | S1 and (MOSFET) | US-PGPUB; USPAT; USOCR; JPO | OR | ON | 2005/05/16 14:12 |
| S3 | 353 | S1 and (MOSFET or "metal oxide semiconductor field effect transistor") | US-PGPUB; USPAT; USOCR; JPO | OR | ON | 2005/05/19 10:33 |
| S6 | 327 | (438/294).CCLS. | US-PGPUB; USPAT; USOCR; JPO | OR | OFF | 2005/05/16 14:58 |
| S7 | 103 | S6 and (MOSFET or "metal oxide semiconductor field effect transistor") | US-PGPUB; USPAT; USOCR; JPO | OR | ON | 2005/05/16 15:26 |
| S9 | 714 | (438/296).CCLS. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/05/16 15:26 |
| S10 | 171 | S9 and (MOSFET or "metal oxide semiconductor field effect transistor") | US-PGPUB; USPAT; USOCR; JPO | OR | ON | 2005/05/16 16:04 |
| S11 | 1453 | (438/424).CCLS. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/05/16 16:04 |
| S12 | 225 | S11 and (MOSFET or "metal oxide semiconductor field effect transistor") | US-PGPUB; USPAT; USOCR; JPO | OR | ON | 2005/05/16 16:39 |
| S13 | 222 | S12 and (trench near\$5 isolat\$5) | US-PGPUB; USPAT; USOCR; JPO | OR | ON | 2005/05/16 16:40 |
| S14 | 1128 | (438/197).CCLS. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/05/16 16:39 |
| S15 | 434 | S14 and (MOSFET or "metal oxide semiconductor field effect transistor") | US-PGPUB; USPAT; USOCR; JPO | OR | ON | 2005/05/16 16:39 |

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| S16 | 343 | S15 and (trench near\$5 isolat\$5) | US-PGPUB; USPAT; USOCR; JPO | OR | ON | 2005/05/16 16:40 |
| S17 | 0 | ("2004/0126948").URPN. | USPAT | OR | ON | 2005/05/16 17:08 |
| S18 | 0 | ("2004/0126948").URPN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/16 17:08 |
| S19 | 0 | ("2004/0126948").URPN. | USPAT | OR | ON | 2005/05/17 11:58 |
| S25 | 1 | ("6689664").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/05/17 13:11 |
| S26 | 177 | (438/218).CCLS. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/05/17 13:22 |
| S27 | 80849 | MOSFET | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 13:22 |
| S28 | 1230 | S27 and (recess groove trench opening) same gate same (W tungsten refractory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 13:25 |
| S29 | 1113 | S28 and ("257"/\$.ccls. or "438"/\$.ccls.) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 13:26 |
| S30 | 1 | S28 and (barrier refractory) same oxid\$5 same prevent\$3 same (extigate extend\$5 near5 trench near5 isolat\$3 near5 gate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 13:29 |
| S31 | 1 | S27 and (barrier refractory) same oxid\$5 same prevent\$3 same (extigate extend\$5 near5 trench near5 isolat\$3 near5 gate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 13:30 |
| S32 | 477 | S27 and oxid\$5 near7 (polysilicon silicon) same (sidewall wall) same (barrier refractory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 14:12 |

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| S33 | 77 | S28 and oxid\$5 near7 (polysilicon silicon) same (sidewall wall) same (barrier refractory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 14:05 |
| S34 | 13 | S29 and (extigate extend\$5 near5 trench near5 isolat\$4 near5 gate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 14:11 |
| S35 | 11 | S29 and (extend\$5 near5 trench near5 isolat\$4 near5 gate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 14:11 |
| S36 | 76 | S29 and oxid\$5 near7 (polysilicon silicon) same (sidewall wall) same (barrier refractory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 14:14 |
| S37 | 993 | S29 and oxid\$5 near7 (polysilicon silicon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 14:15 |
| S38 | 3 | S37 and extigate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 14:15 |
| S39 | 404 | S29 and (barrier refractory) same oxid\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 14:16 |
| S40 | 382 | S39 and oxid\$5 near7 (polysilicon silicon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 14:17 |
| S41 | 244 | S39 and oxid\$5 near7 (polysilicon silicon) same (sidewall wall) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 15:27 |
| S42 | 1 | ("4685196").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/05/17 15:53 |

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| S43 | 3180 | S27 and (prevent\$3 inhibit\$3) same (short\$3 near3 (electrical circuit) resist\$5 near3 (increas\$3 ris\$3)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 15:57 |
| S44 | 50 | S43 and oxid\$5 near7 (polysilicon silicon) same (sidewall wall) same (barrier refractory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 16:06 |
| S45 | 3010 | S43 and (gate semiconductor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 16:07 |
| S46 | 2 | S43 and extigate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/17 16:07 |
| S47 | 76 | (438/219).CCLS. | US-PGPUB; USPAT; USOCR; JPO | OR | OFF | 2005/05/18 10:35 |
| S48 | 314 | (438/221).CCLS. | US-PGPUB; USPAT; USOCR; JPO | OR | OFF | 2005/05/18 10:36 |
| S49 | 74 | S48 and MOSFET | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/18 10:47 |
| S50 | 135 | (438/223).CCLS. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/05/18 14:12 |
| S51 | 227 | (438/230).CCLS. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/05/18 14:12 |
| S52 | 80849 | MOSFET | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/18 16:35 |
| S53 | 4 | S52 and EXTIGATE | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/18 16:35 |

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| S54 | 42 | S52 and (EXTIGATE extend\$5 near5 trench near5 isolat\$3 near5 gate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/18 16:37 |
| S55 | 1 | ("20040075138").PN. | US-PGPUB; USPAT; USOCR; JPO | OR | OFF | 2005/05/19 10:03 |
| S56 | 1 | ("6838326").PN. | US-PGPUB; USPAT; USOCR; JPO | OR | OFF | 2005/05/19 10:32 |
| S57 | 1185 | (438/303).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/19 10:32 |
| S58 | 473 | S57 and MOSFET | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/19 10:33 |
| S59 | 483 | S57 and (MOSFET or "metal oxide semiconductor field effect transistor") | US-PGPUB; USPAT; USOCR; JPO | OR | ON | 2005/05/19 13:42 |
| S60 | 510 | (438/299).CCLS. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/05/19 13:42 |
| S61 | 507 | (438/299).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/19 13:42 |
| S62 | 186 | S60 and MOSFET | US-PGPUB; USPAT; USOCR | OR | ON | 2005/05/19 15:44 |
| S63 | 907 | (438/275).CCLS. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/05/19 15:44 |
| S64 | 251 | S63 and MOSFET | US-PGPUB; USPAT; USOCR | OR | ON | 2005/05/20 10:24 |
| S65 | 1058 | (438/287).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/20 10:25 |

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| S66 | 253 | S65 and MOSFET | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/20 10:25 |
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| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|--|---|------------------|---------|------------------|
| L2 | 61528 | mosfet metal adj oxide near5 field adj effect | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/05/23 10:53 |
| L3 | 3738 | 2 and (trench opening groove recess hole) near5 fill\$3 near5 (isolat\$3 dielectric insulating oxide dioxide nitride sin sio2 "sio?sub.2" n>"sub.4") | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/05/23 11:00 |
| L4 | 859 | 3 and (oxide dioxide sio2 "sio?sub.2") same (sidewall wall) near7 (polysilicon silicon) same gate | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/05/23 11:21 |
| L5 | 799 | 4 and (trench opening groove recess hole) same gate | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/05/23 11:01 |
| L6 | 8 | 5 and (prevent\$3 eliminat\$3 inhibit\$3) near7 oxid\$5 near5 (metal barrier) same (w tungsten) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/05/23 11:04 |
| L7 | 8 | 6 and (prevent\$3 eliminat\$3 inhibit\$3) near7 oxid\$5 near5 (metal barrier) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/05/23 11:04 |
| L8 | 8776 | ("257"/\$.ccls. "438"/\$.ccls. "427"/\$.ccls.) and (sti trench near3 isolat\$4) same gate | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/05/23 11:17 |
| L9 | 3136 | 8 and (sti trench near3 isolat\$4) near7 (etch\$3 recess\$3 remov\$3) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/05/23 11:19 |
| L10 | 615 | 9 and fill\$3 near5 (sti isolat\$4) near7 (etch\$3 recess\$3 remov\$3) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/05/23 11:20 |
| L11 | 115 | 10 and (oxide dioxide sio2 "sio?sub.2") same (sidewall wall) near7 (polysilicon silicon) same gate | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/05/23 11:21 |
| L12 | 100 | 11 not (@rlad>"20031215" @ad>"20031215") | US-PGPUB; USPAT; EPO; JPO | OR | OFF | 2005/05/23 11:22 |